

Silicon PNP Power Transistors

2SB886

DESCRIPTION

- With TO-220C package
- Complement to type 2SD1196
- DARLINGTON
- High DC current gain
- High current capacity and wide ASO
- Low saturation voltage

APPLICATIONS

- Motor drivers, printer
- Hammer drivers
- Relay drivers,
- Voltage regulator control.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

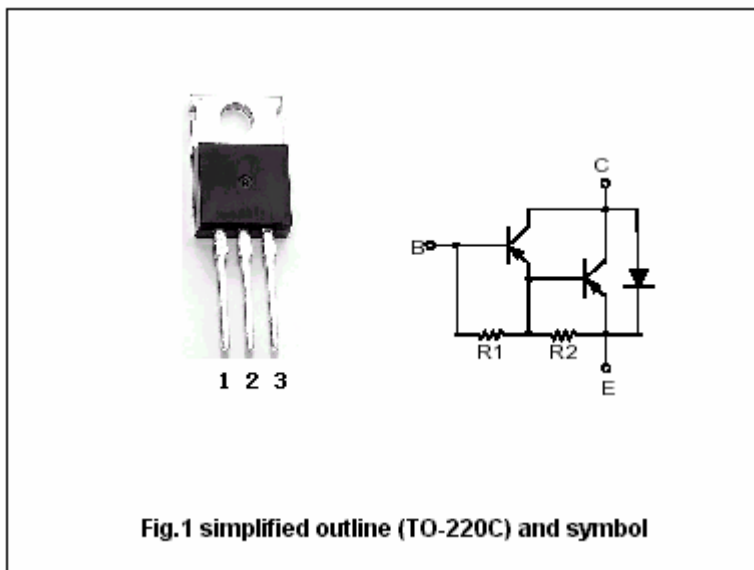


Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-110	V
V _{CEO}	Collector-emitter voltage	Open base	-100	V
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current (DC)		-8	A
I _{CM}	Collector current-Peak		-12	A
P _C	Collector dissipation	T _C =25°C	40	W
			1.75	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-50~150	°C

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CHARACTERISTICS

T_j=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA; R _{BE} =∞	-100			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-5mA; I _E =0	-110			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-4A; I _B =-8mA		-1.0	-1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-4A; I _B =-8mA			-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-80V; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-3.0	mA
f _T	Transition frequency	I _C =-4A ; V _{CE} =-5V		20		MHz
h _{FE}	DC current gain	I _C =-4A ; V _{CE} =-3V	1500	4000		

Switching times

t _{on}	Turn-on time	I _C =-4A; I _{B1} =-I _{B2} =-8mA R _L =12.5Ω, Duty cycle≤1% V _{CC} =50V		0.7		μs
t _{stg}	Storage time			1.4		μs
t _f	Fall time			1.5		μs

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PACKAGE OUTLINE



Fig.2 Outline dimensions (unindicated tolerance:±0.10mm)